Central™
Semiconductor Corp.

PROCESS CP611

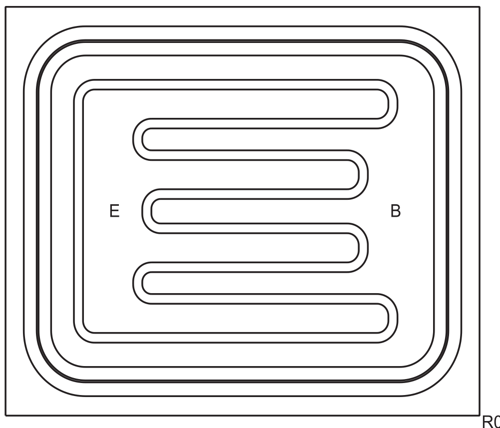
Power Transistor

PNP - Amp/Switch Transistor Chip

PROCESS DETAILS

Process	EPITAXIAL BASE
Die Size	80 X 99 MILS
Die Thickness	12.5 ± 1 MILS
Base Bonding Pad Area	12 X 32 MILS
Emitter Bonding Pad Area	13 X 46 MILS
Top Side Metalization	Al - 50,000Å
Back Side Metalization	Cr/Ni/Ag - 16,000Å

GEOMETRY



BACKSIDE COLLECTOR

GROSS DIE PER 4 INCH WAFER

1,450

PRINCIPAL DEVICE TYPES

CJD42C
TIP42C

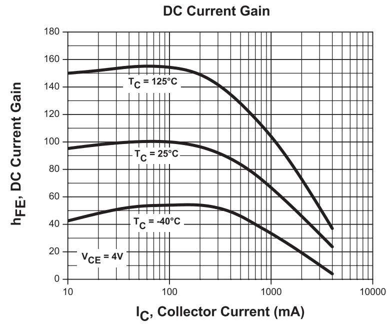
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

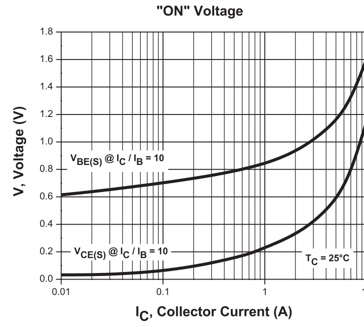
R4 (21-August 2006)

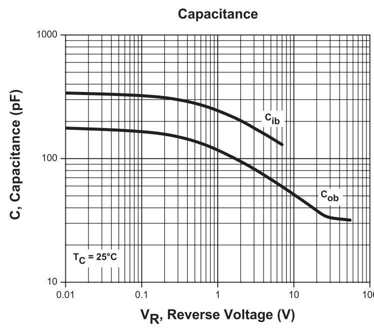
Central™ Semiconductor Corp.

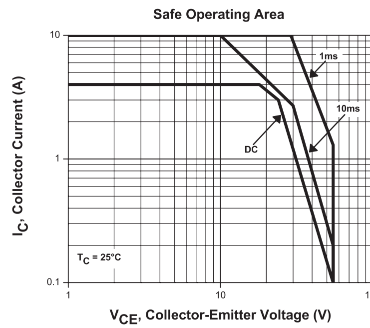
PROCESS CP611

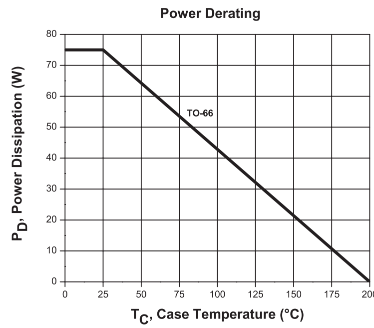
Typical Electrical Characteristics

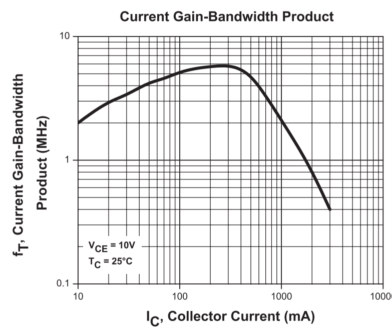












145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centralsemi.com

R4 (21-August 2006)